

TOSHIBA Field Effect Transistor Silicon N Channel Junction Type

# 2SK371

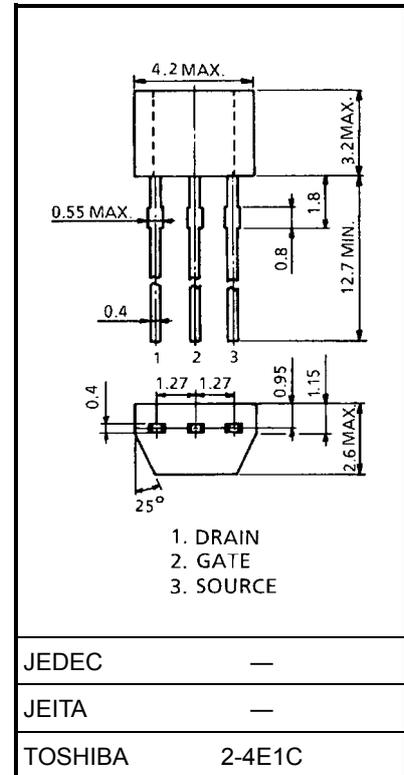
For Low Noise Audio Amplifier Applications

Unit: mm

- Suitable for use as first stage for equalizer and MC head amplifiers.
- High  $|Y_{fs}|$ :  $|Y_{fs}| = 40 \text{ mS (typ.)}$  ( $V_{DS} = 10 \text{ V}$ ,  $V_{GS} = 0$ ,  $I_{DSS} = 5 \text{ mA}$ )
- High breakdown voltage:  $V_{GDS} = -40 \text{ V}$
- Super low noise:  $NF = 1.0\text{dB (typ.)}$   
( $V_{DS} = 10 \text{ V}$ ,  $I_D = 0.5 \text{ mA}$ ,  $f = 1 \text{ kHz}$ ,  $R_G = 100 \Omega$ )
- High input impedance:  $I_{GSS} = -1 \text{ nA (max)}$  ( $V_{GS} = -30 \text{ V}$ )
- Small package

### Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

Characteristics	Symbol	Rating	Unit
Gate-drain voltage	$V_{GDS}$	-40	V
Gate current	$I_G$	10	mA
Drain power dissipation	$P_D$	200	mW
Junction temperature	$T_j$	125	$^\circ\text{C}$
Storage temperature range	$T_{stg}$	-55~125	$^\circ\text{C}$



### Electrical Characteristics ( $T_a = 25^\circ\text{C}$ )

Weight: 0.13 g (typ.)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Gate cut-off current	$I_{GSS}$	$V_{GS} = -30 \text{ V}$ , $V_{DS} = 0$	—	—	-1.0	nA
Gate-drain breakdown voltage	$V_{(BR)GDS}$	$V_{DS} = 0$ , $I_G = -100 \mu\text{A}$	-40	—	—	V
Drain current	$I_{DSS}$ (Note 1)	$V_{DS} = 10 \text{ V}$ , $V_{GS} = 0$	5.0	—	30	mA
Gate-source cut-off voltage	$V_{GS(OFF)}$	$V_{DS} = 10 \text{ V}$ , $I_D = 0.1 \mu\text{A}$	-0.3	—	-1.2	V
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = 10 \text{ V}$ , $V_{GS} = 0$ , $f = 1 \text{ kHz}$ , (typ.: $I_{DSS} = 5 \text{ mA}$ )	25	40	—	mS
Input capacitance	$C_{iss}$	$V_{DS} = 10 \text{ V}$ , $V_{GS} = 0$ , $f = 1 \text{ MHz}$	—	75	—	pF
Reverse transfer capacitance	$C_{rss}$	$V_{DG} = 10 \text{ V}$ , $I_D = 0$ , $f = 1 \text{ MHz}$	—	15	—	pF
Noise figure (Note 2)	NF (1)	$V_{DS} = 10 \text{ V}$ , $R_G = 100 \Omega$ , $I_D = 5 \text{ mA}$ , $f = 100 \text{ Hz}$	—	5	10	dB
	NF (2)	$V_{DS} = 10 \text{ V}$ , $R_G = 100 \Omega$ , $I_D = 5 \text{ mA}$ , $f = 1 \text{ kHz}$	—	1	2	

Note 1:  $I_{DSS}$  classification GR: 5.0~10.0 mA, BL: 8.0~16.0 mA, V: 14.0~30.0 mA

Note 2: Use this in the low voltage region ( $V_{DS} < 15 \text{ V}$ ) for low noise applications.